

Foreword

For 11 consecutive years, the *Journal of Electronic Materials* has published a special issue on SiC and the group III nitride semiconductors. These materials continue to be the focus of worldwide research and development activity. The scope of the special issue has been expanded this year to include ZnO, in response to growing interest in this wide band gap semiconductor. Twenty-five papers on semiconductor growth, characterization, processing, and device performance are included in this special issue. Many of the papers were also presented at the 46th Electronic Materials Conference (EMC), held in June 2004 at the University of Notre Dame. The conference remains a lively annual forum for the discussion of research on wide band gap semiconductors. Publication of this special issue was made possible only through the efforts of many authors, reviewers, editors, and journal staff members, and we thank them all for their invaluable contributions.

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